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				C mplete If Known	
				Application Number	10/604,747
				Filing Date	August 14, 2003
				First Named Inventor	Herr, Daniel J seph Christian
				Art Unit	
				Examiner Name	
Sheet	1	of		Attorney Docket Number	361007-000025

U.S. PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
MW	AA	5,787,253		7/28/98	McCreery et al.	
MW	AR	6,068,698		5/30/00	Schmidt	
MW	AV	5,981,316		11/09/99	Yamada et al.	

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Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴ -Number ⁴ -Kind Code ⁶ (if known)					
MW	AC	99/13511		3-18-99	Schmidt		
MW	AD	0,781,727		2-7-97	NEC Corp.		

NON PATENT LITERATURE DOCUMENTS

Examiner Initial	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MW	AE	D. M. Eigler et al., "Positioning single atoms with a scanning tunnelling microscope", <i>Nature</i> , Vol. 344 (April 1990) pp 524-526.
MW	AF	P. Bedrossian et al., "Demonstration of the tunnel-diode effect on an atomic", scale, <i>Nature</i> , Vol. 342 (November 1989) pp 258-260.
MW	AG	Nishi Y. ET AL., <i>Handbook of Semiconductor Manufacturing Technology</i> , Marcel Dekker, Inc. New York, NY (2000).
MW	AH	Frank, D. et al., "Device Scaling Limits of SiMOSFETs and Their Application Dependencies," <i>Proceedings of the IEEE</i> , Vol. 89, No. 3, (March 2001).
MW	AI	Gross, W. et al., "Ultrasmall MOSFETs: The Importance of the full Coulomb Interaction on Device Characteristics," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 10, (October 2000).
MW	AJ	Clark, A., "Russian Technology Waves Goodbye to Strained Silicon," <i>EE Times</i> , (April 8, 2002).

Examiner Signature	MW/Ilczeuski	Date Considered	9/2004
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

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<p>Substitute for form 1449B/PTO</p> <p>O I P INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>DEC 18 2003</p> <p>(use as many sheets as necessary)</p>				<p style="text-align: center;">C mplete If Known</p> <table border="1"> <tr> <td>Application Number</td> <td>10/604,747</td> </tr> <tr> <td>Filing Date</td> <td>August 14, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Herr, Daniel Joseph Christian</td> </tr> <tr> <td>Art Unit</td> <td></td> </tr> <tr> <td>Examiner Name</td> <td></td> </tr> </table>		Application Number	10/604,747	Filing Date	August 14, 2003	First Named Inventor	Herr, Daniel Joseph Christian	Art Unit		Examiner Name	
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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²										
MW	AK	Feynman, R.P., Infinitesimal Machinery, <i>Journal of MicroMechanical Systems</i> , Vol. 2, No. 1, March 1993, pp. 4-14.													
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MW	AW	Desiraju, G.R. (Ed.), "Thoughts on Crystals as Supramolecules", <i>The Crystal as a Supramolecular Entity</i> , John Wiley and Sons Ltd., 1996.													
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Examiner Signature	MW/czewski	Date Considered	9/2004
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